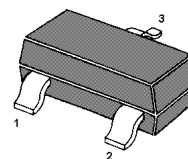


C1815 TRANSISTOR (PNP)

FEATURES

- Complementary to A1015
- Power Dissipation of 200mW
- High Stability and High Reliability

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

Marking: HF

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.15	A
P_C	Collector Power Dissipation	0.2	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

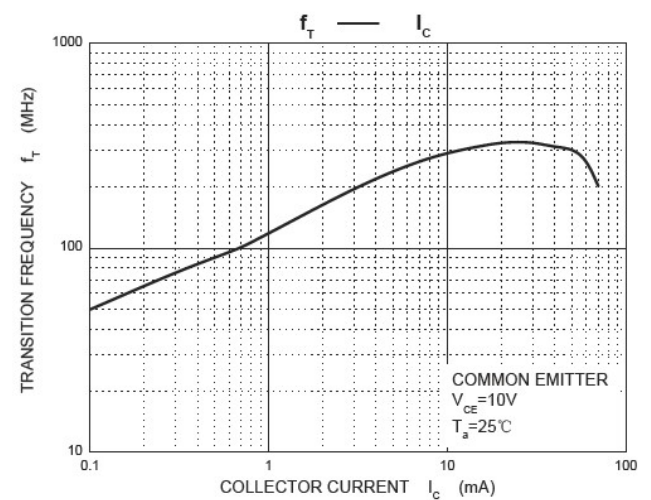
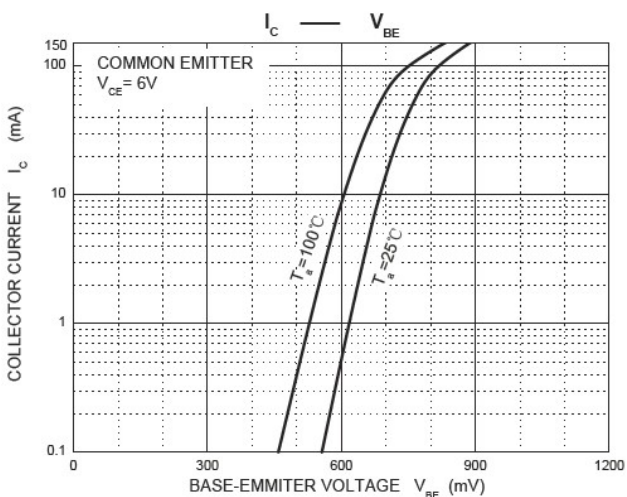
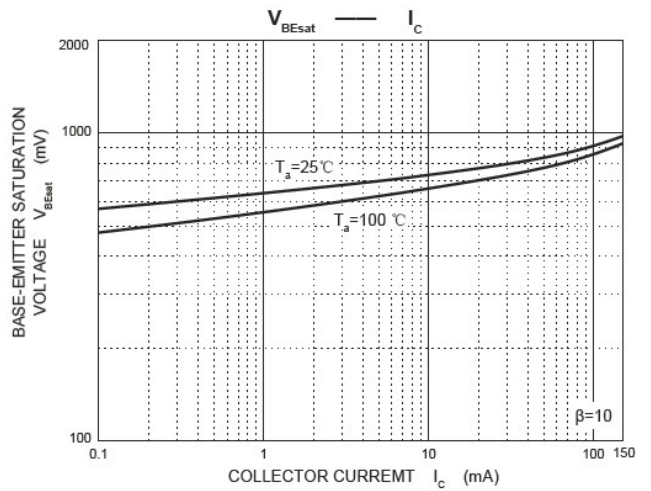
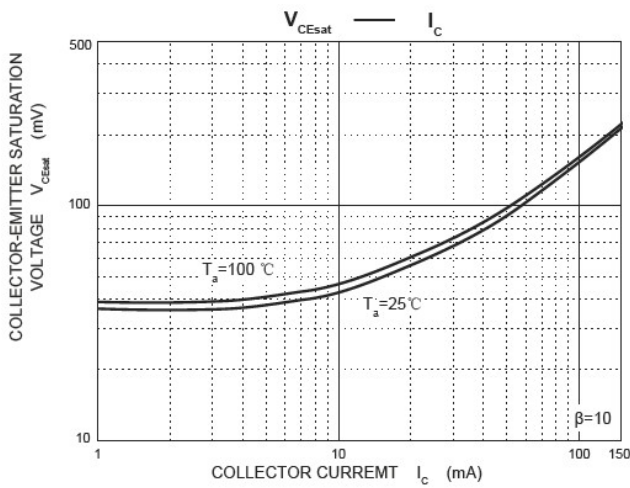
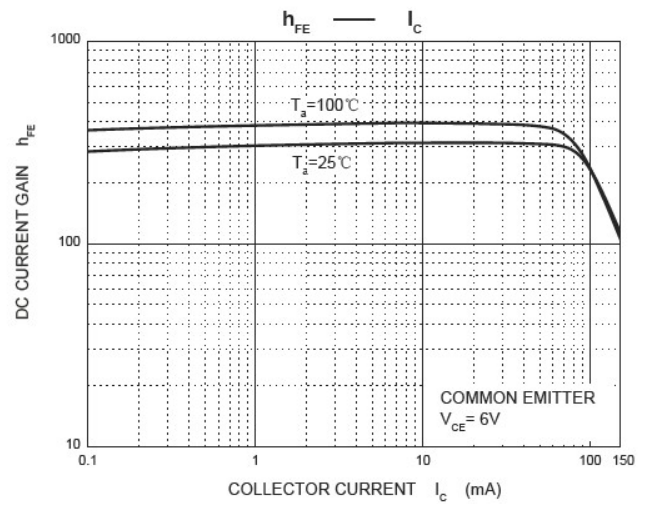
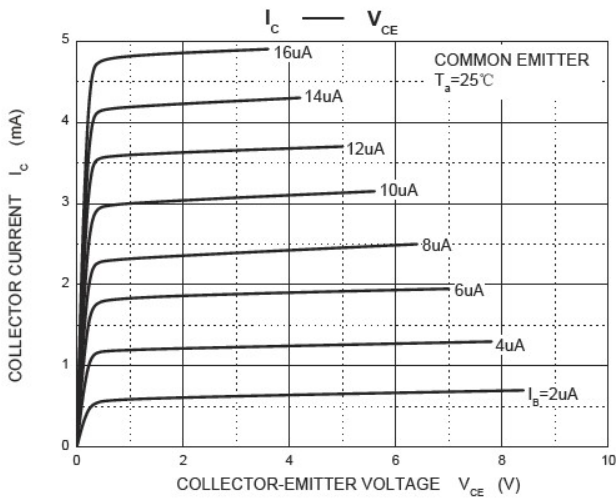
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

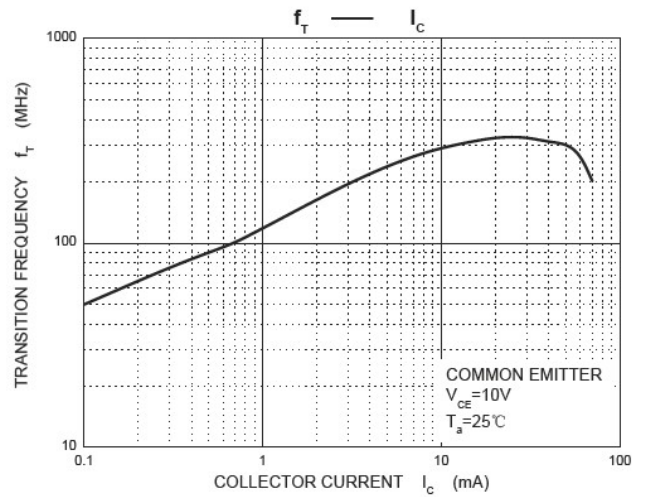
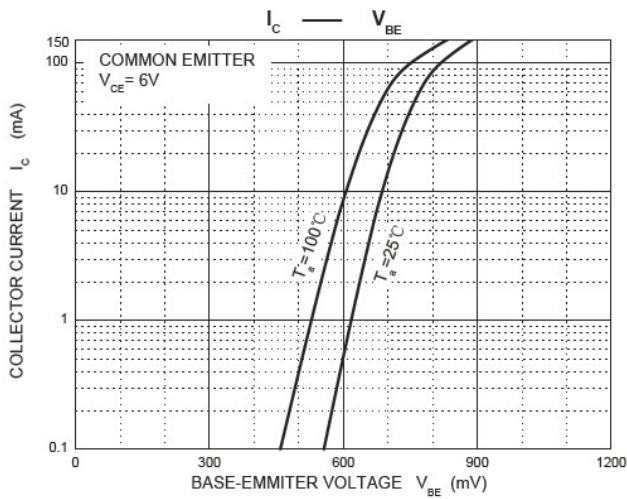
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C=100\mu\text{A}$, $I_E=0$	60		V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=0.1\text{mA}$, $I_B=0$	50		V
Emitter-base breakdown voltage	V_{EBO}	$I_E=100\mu\text{A}$, $I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}$, $I_E=0$		100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$		100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=6\text{V}$, $I_C=2\text{mA}$	130	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}$, $I_B=10\text{mA}$		0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}$, $I_B=10\text{mA}$		1.00	V
Transition frequency	f_T	$V_{CE}=10\text{V}$, $I_C=1\text{mA}$ $f=30\text{MHz}$	80		MHz

CLASSIFICATION OF h_{FE}

HFE	130-400	
RANK	L	H
RANGE	130-200	200-400

Typical Characteristics





PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

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